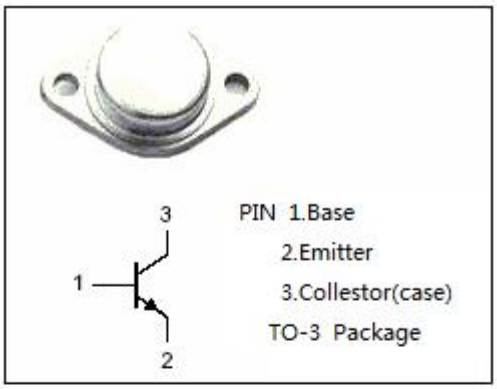
isc Silicon NPN Power Transistor — BU132

DESCRIPTION

- Excellent Safe Operating Area
- Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= 1.0 V(Max)@ I_C = 0.5A
- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= 600V(Min)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

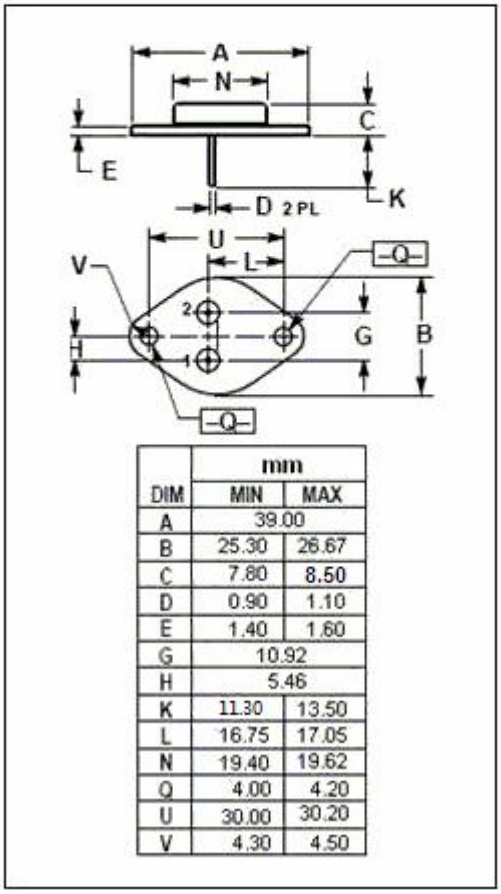


APPLICATIONS

- Designed for general-purpose switching and amplifier applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	800	V
V_{CEO}	Collector-Emitter Voltage	600	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	1	A
I_{CM}	Collector Current-Peak	2	A
P_C	Collector Power Dissipation@T_C=25℃	15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~150	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA ; I_B= 0	600			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 1mA; I_E= 0	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 0.5A; I_B= 50mA			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 0.5A; I_B= 50mA			1.5	V
I_{CBO}	Collector Base Cutoff Current	V_{CB}=800V; I_E= 0			0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6V; I_C= 0			0.1	mA
h_{FE}	DC Current Gain	I_C= 0.25A ; V_{CE}= 10V	25		125	
f_T	Current Gain-Bandwidth Product	I_C= 0.5A ; V_{CE}= 10V		8		MHz